TOSHIBA PHOTOCOUPLER GaAs IRED & PHOTO-TRIAC

TLP3041(S),TLP3042(S),TLP3043(S)

OFFICE MACHINE
HOUSEHOLD USE EQUIPMENT
TRIAC DRIVER
SOLID STATE RELAY

The TOSHIBA TLP3041 (S), TLP3042 (S), TLP3043 (S) consist of a zero voltage crossing turn-on photo-triac optically coupled to a gallium arsenide infrared emitting diode in a six lead plastic DIP package. All parameters are tested to the specification of TLP3041, TLP3042, TLP3043.

• Peak Off-State Voltage : 400 V (min)

• Trigger LED Current : 15 mA (max) (TLP3041)

10 mA (max) (TLP3042) 5 mA (max) (TLP3043)

• On-State Current : 100 mA (max)

• UL Recognized : UL1577, File No. E67349

• Isolation Voltage : 5000 Vrms (min)

Option (D4) Type

VDE Approved : DIN VDE0884 / 06.92

Certificate No. 68329

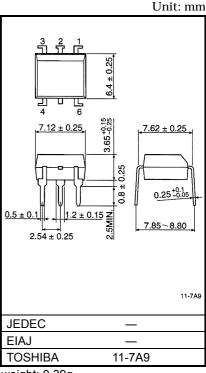
Maximum Operating Insulation Voltage : 890 Vpk Highest Permissible Over Voltage : 8000 Vpk

Note: When a VDE0884 approved type is needed,please designate the "Option (D4)"

- p...-. (= .)

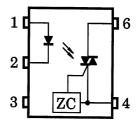
• Device Construction

	7.62mm pich	10.16 mm pich			
	standard type	(LF2) type			
Creepage Distance	7.0 mm (min)	8.0 mm (min)			
Clearance	7.0 mm (min)	8.0 mm (min)			
Insulation Thickness	0.5 mm (min)	0.5 mm (min)			



weight: 0.39g

PIN CONFIGURATION (Top view)



- 1: ANODE
- 2: CATHODE
- 3: N.C.
- 4: TERMINAL 1
- 6: TERMINAL 2



MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC			SYMBOL	RATING	UNIT
Forward Current			lF	50	mA
	Forward Current Derati (Ta ≥ 53°C)	ing	ΔI _F / °C	-0.7	mA / °C
	Peak Forward Current (100 μ s pulse, 100pps)		I _{FP}	1	А
E	Power Dissipation		P_{D}	100	mW
	Power Dissipation Dera (Ta ≥ 25°C)	ating	ΔP _D / °C	-1.0	mW / °C
Reverse Voltage			V _R	5	V
	Junction Temperature		Tj	125	°C
	Off-State Output Termi	nal Voltage	V_{DRM}	400	V
	On-Stage RMS	Ta = 25°C	1	100	m A
	Current	Ta = 70°C	I _{T(RMS)}	50	- mA
~	On-State Current Dera (Ta ≥ 25°C)	ting	ΔI _T / °C	-1.1	mA / °C
DETECTOR	Peak On-Stage Curren (100 µs pulse, 120 pps)	t	I _{TP}	2	А
DET	Peak Nonrepetitive Sur Current (P _W = 10ms, D		I _{TSM}	1.2	А
	Power Dissipation		P_{D}	300	mW
	Power Dissipation Dera (Ta ≥ 25°C)	ating	ΔP _D / °C	-4.0	mW / °C
	Junction Temperature		Tj	115	°C
Storage Temperature Range			T _{stg}	– 55 ~ 150	°C
Operating Temperature Range			T _{opr}	−40 ~ 100	°C
Lead Soldering Temperature (10s)			T _{sol}	260	°C
Total Package Power Dissipation			P _T	330	mW
Total Package Power Dissipation Derating (Ta ≥ 25°C)			ΔP _T / °C	-4.4	mW / °C
	tion Voltage 1 min., R.H. ≤ 60%)	BV _S	5000	Vrms	

Note 1: Device considered a two terminal device: Pins 1, 2 and 3 shorted together and pins 4 and 6 shorted together.

RECOMMENDED OPERATING CONDISTIONS

CHARACTERISTIC	SYMBOL	MIN	TYP.	MAX	UNIT
Supply Voltage	V_{AC}	_	_	120	Vac
Forward Current	I _F *	15	20	25	mA
Peak On-Stage Current	I _{TP}	_	_	1	Α
Operating Temperature	T _{opr}	-25	_	85	°C

*: In the case of TLP3042



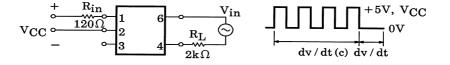
INDIVIDUAL ELECTRICAL CHARACTERISTICS (Ta = 25°C)

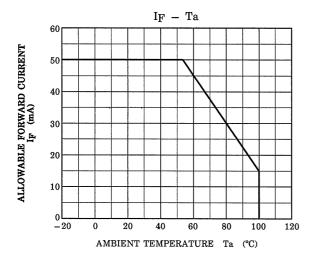
	CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP.	MAX	UNIT
	Forward Voltage	V _F	I _F = 10mA	1.0	1.15	1.3	V
LED	Reverse Current	I _R	V _R = 5V	_	_	10	μΑ
	Capacitance	C _T	V = 0, f = 1MHz	_	10	_	pF
DETECTOR	Peak Off-State Current	I _{DRM}	V _{DRM} = 400V	_	10	100	nA
	Peak On-Stage Voltage	V_{TM}	I _{TM} = 100mA	_	1.7	3.0	V
	Holding Current	lΗ	_	_	0.6	_	mA
	Critical Rate of Rise of Off- State Voltage	dv / dt	V _{in} = 120Vrms, Ta = 85°C (Fig.1)	200	500	_	V / μs
	Critical Rate of Rise of Commutating Voltage	dv / dt(c)	V _{in} = 30Vrms, IT = 15mA (Fig.1)	_	0.2	_	V / μs

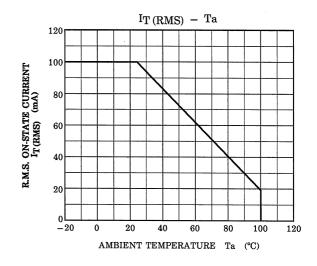
COUPLED ELECTRICAL CHARACTERISTICS (Ta = 25°C)

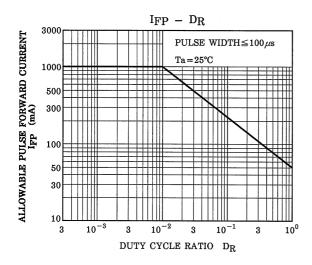
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN	TYP.	MAX	UNIT
	TLP3041	I _{FT}	V _T = 3V	_	_	15	mA
Trigger LED Current	TLP3042			_	5	10	
	TLP3043			_	_	5	
Inhibit Voltage		V _{IH}	I _F = Rated I _{FT}	_	_	40	V
Leakage in Inhibited State		lін	I _F = Rated I _{FT} V _T = Rated V _{DRM}	_	100	300	μΑ
Capacitance Input to Output		CS	V _S = 0, f = 1MHz	_	0.8	_	pF
Isolation Resistance		R _S	V _S = 500V (R.H. ≤ 60%)	5×10 ¹⁰	10 ¹⁴	_	Ω
			AC, 1 minute	5000	_	_	Vrms
Isolation Voltage		BV_S	AC, 1 second (in oil)	_	10000	_	VIIIIS
			DC, 1 minute (in oil)	_	10000	_	Vdc

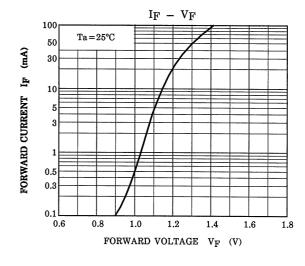
Fig. 1 dv / dt TEST CIRCUIT

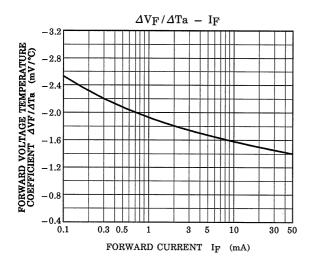


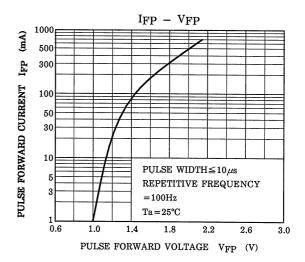




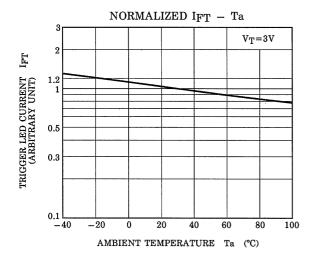


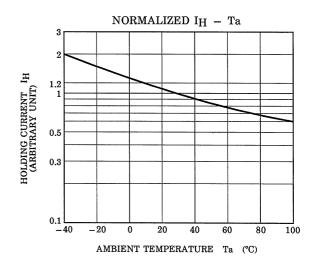


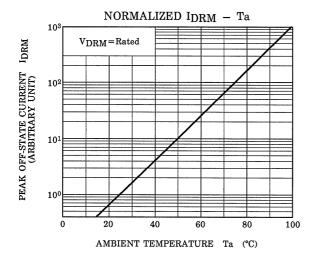


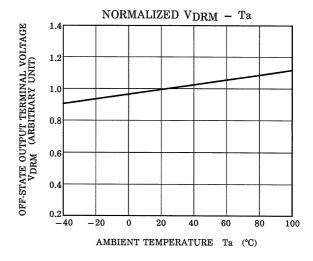


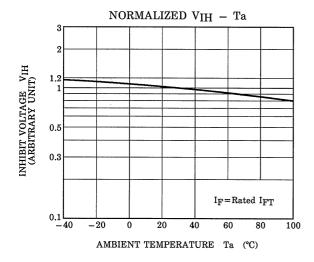
4

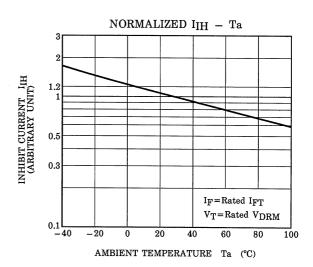












RESTRICTIONS ON PRODUCT USE

000707EBC

- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc..
- The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.). These TOSHIBA products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of TOSHIBA products listed in this document shall be made at the customer's own risk.
- Gallium arsenide (GaAs) is a substance used in the products described in this document. GaAs dust and fumes
 are toxic. Do not break, cut or pulverize the product, or use chemicals to dissolve them. When disposing of the
 products, follow the appropriate regulations. Do not dispose of the products with other industrial waste or with
 domestic garbage.
- The products described in this document are subject to the foreign exchange and foreign trade laws.
- The information contained herein is presented only as a guide for the applications of our products. No
 responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other
 rights of the third parties which may result from its use. No license is granted by implication or otherwise under
 any intellectual property or other rights of TOSHIBA CORPORATION or others.
- The information contained herein is subject to change without notice.